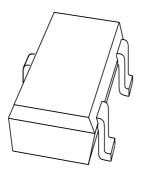
DISCRETE SEMICONDUCTORS

DATA SHEET



PMSTA92 PNP high-voltage transistor

Product data sheet Supersedes data of 1999 Jun 01 2001 Feb 20



PNP high-voltage transistor

PMSTA92

FEATURES

- S-mini package
- · High voltage.

APPLICATIONS

• Primarily intended for use in telephony and professional communication equipment.

DESCRIPTION

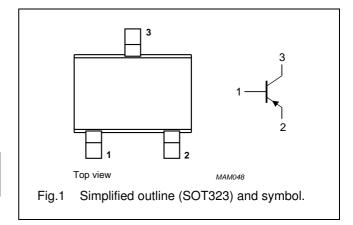
PNP transistor in a microminiature (SMD) plastic package intended for surface mounted applications.

MARKING

TYPE NUMBER	MARKING CODE	
PMSTA92	tD2	

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-300	٧
V _{CEO}	collector-emitter voltage	open base	_	-300	٧
V _{EBO}	emitter-base voltage	open collector	_	- 5	٧
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		-	-200	mA
I _{BM}	peak base current		-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	625	K/W	

Note

1. Refer to SOT323 (SC-70) standard mounting conditions.

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CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$V_{CB} = -200 \text{ V}; I_E = 0$	_	_	-100	nA
I _{EBO}	emitter cut-off current	$V_{BE} = -3 \text{ V}; I_{C} = 0$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -1 \text{ mA}; V_{CE} = -10 \text{ V}$	40	_	_	
		$I_C = -10 \text{ mA}; V_{CE} = -10 \text{ V}$	40	_	_	
		$I_C = -30 \text{ mA}; V_{CE} = -10 \text{ V}$	30	_	_	
V _{CEsat}	saturation voltage	$I_C = -20 \text{ mA}$; $I_B = -2 \text{ mA}$; note 1	_	_	-250	mV
V _{BEsat}	saturation voltage	$I_C = -20 \text{ mA}$; $I_B = -2 \text{ mA}$; note 1	_	_	-900	mV
C _c	collector-base capacitance	$V_{CB} = -20 \text{ V}; I_E = i_e = 0; f = 1 \text{ MHz}$	_	1.9	3.5	pF
C _e	emitter-base capacitance	$V_{EB} = -5 \text{ V}; I_C = i_C = 0; f = 1 \text{ MHz}$	_	20	_	pF
f _T	transition frequency	$V_{CE} = -20 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	50	_	_	MHz

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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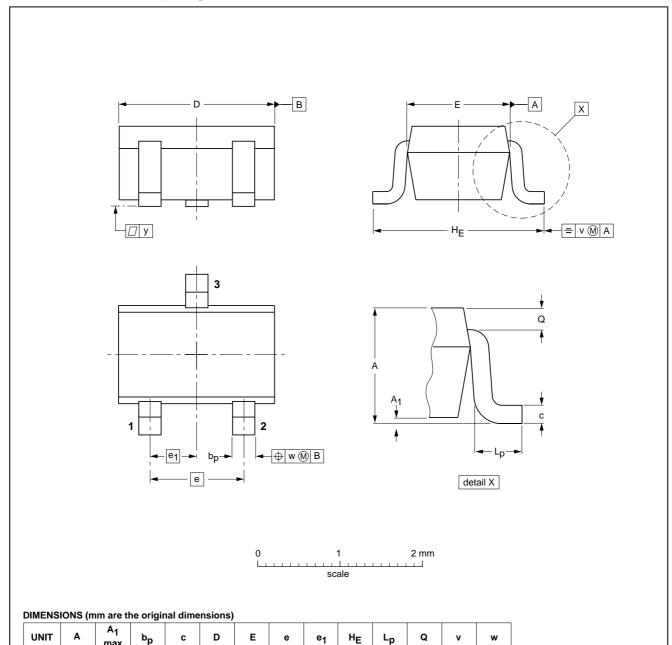
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT323			SC-70			97-02-28

0.65

2.2 2.0 0.23 0.13

0.2

0.45

0.15

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0.4 0.3

1.1

mm

0.1

0.25

0.10

2.2

1.8

1.35

1.15

1.3

PNP high-voltage transistor

PMSTA92

DATA SHEET STATUS

DOCUMENT STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

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Printed in The Netherlands 613514/03/pp6 Date of release: 2001 Feb 20 Document order number: 9397 750 07875

